Lam Breaks New Ground to Advance Silicon Etch for Sub-90 nm Processes

FREMONT, Calif., September 25, 2002—Lam Research Corporation (Nasdaq: LRCX) today launched the 2300 Versys Star silicon etch system for 200 and 300 mm applications. Building on the success of Lam's market-leading 2300 Versys, the 2300 Versys Star expands process capability for etching the complex structures required for sub-90 nm applications. The new system introduces unique technologies for rapidly controlling temperature and gas flow step-by-step across the wafer surface to meet next-generation CD uniformity requirements. For a typical gate etch process, applying these new tuning capabilities of the 2300 Versys Star reduces CD variation by as much as 50%.

"This latest achievement demonstrates Lam's continued technology leadership and differentiation to solidify our position as number one in market share for silicon etch. No other silicon etch system in the industry offers this level of process control and wide process window to address next-generation process challenges. The 2300 Versys Star is in production at major foundries and has also shipped to logic and memory fabs in key regions around the world," stated Nick Bright, Lam's vice president and general manager of global products.

The 2300 Versys Star enables in situ etching of complex film stacks, such as resist trim followed by antireflective coating (ARC) and hardmask open over dual-doped polysilicon gate as well as shallow trench isolation (STI) etch. The system's new capabilities to rapidly tune wafer temperature and gas flow offer flexibility and step-by-step uniformity control to optimize each layer of the complex stack, delivering enhanced performance and productivity.

This press release contains certain forward-looking statements which are subject to the Safe Harbor provisions created by the Private Securities Litigation Reform Act of 1995. Such forward-looking statements relate to next-generation process requirements and results, market share estimates and machine performance, among others. Such statements are based on current expectations and are subject to risks, uncertainties and changes in condition, significance, value and effect as well as other risks detailed in documents filed with the Securities and Exchange Commission, including specifically the report on Form 10-K for the year ended June 30, 2002, which could cause actual results to vary from expectations. The company undertakes no obligation to update the information or statements made in this press release.

Lam Research Corporation is a leading supplier of wafer fabrication equipment and services to the world's semiconductor industry. Lam's common stock trades on the Nasdaq National Market under the symbol LRCX. The Company's World Wide Web address is http://www.lamrc.com.

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